

PHPT610030NK-QX Datasheet



DiGi Electronics Part Number

PHPT610030NK-QX-DG

Manufacturer

Nexperia USA Inc.

Manufacturer Product Number

PHPT610030NK-QX

Description

PHPT610030NK-Q/SOT1205/LFPAK56

Detailed Description

Bipolar (BJT) Transistor Array 2 NPN (Dual) 100V 3A

140MHz 1W Surface Mount LFPAK56D

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PHPT610030NK-QX	Nexperia USA Inc.
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
2 NPN (Dual)	3A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
100V	330mV @ 300mA, 3A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
100nA	150 @ 500mA, 10V
Power - Max:	Frequency - Transition:
1W	140MHz
Operating Temperature:	Grade:
175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
SOT-1205, 8-LFPAK56	LFPAK56D
Base Product Number:	
PHPT610030	

Environmental & Export classification

RoHS Status:	REACH Status:
ROHS3 Compliant	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.29.0075

1. General description

NPN/NPN high power double bipolar transistor in a SOT1205 (LFPAK56D) Surface-Mounted Device (SMD) power plastic package.

2. Features and benefits

- · High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- · Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Motor control
- Power management
- · Load switch
- Linear mode voltage regulator
- Backlighting applications
- · Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transistor						
V _{CEO}	collector-emitter voltage	open base	-	-	100	V
I _C	collector current		-	-	3	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 3 A; I_B = 0.3 A; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	75	110	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1	8 7 6 5	
2	B1	base TR1	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	C1 B2 E2
3	E2	emitter TR2		
4	B2	base TR2		(TR2)
5	C2	collector TR2		TRI
6	C2	collector TR2		E1 B1 C2
7	C1	collector TR1		sym140
8	C1	collector TR1	LFPAK56D; Dual LFPAK (SOT1205)	Зушто

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PHPT610030NK-Q	LFPAK56D; Dual LFPAK	plastic, single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT610030NK-Q	10030NK

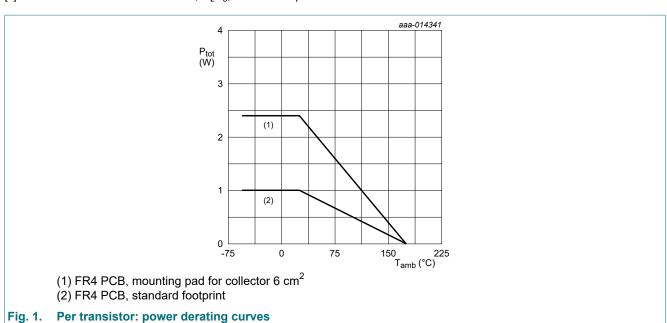
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or				'	
V _{CBO}	collector-base voltage	open emitter		-	100	V
V _{CEO}	collector-emitter voltage	open base		-	100	V
V _{EBO}	emitter-base voltage	open collector		-	7	V
I _C	collector current			-	3	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	Α
I _B	base current			-	0.5	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1	W
			[2]	-	2.4	W
			[3]	-	25	W
Per device	<u> </u>		,	'		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.25	W
			[4]	-	5	W
			[2]	-	3	W
T _j	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Power dissipation from junction to mounting base.
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor		'				
$R_{\text{th(j-a)}}$	thermal resistance from	in free air	[1]	-	-	150	K/W
	junction to ambient		[2]	-	-	62.5	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	6	K/W
Per device				1			
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	120	K/W
	junction to ambient		[2]	-	-	50	K/W
			[3]	-	-	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

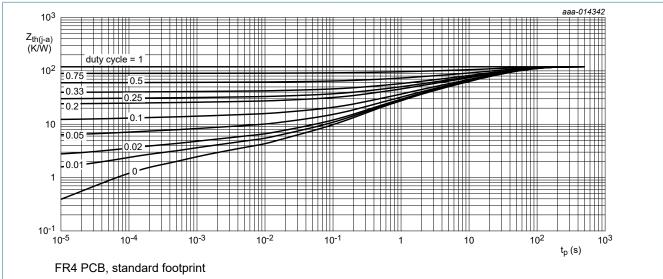


Fig. 2. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

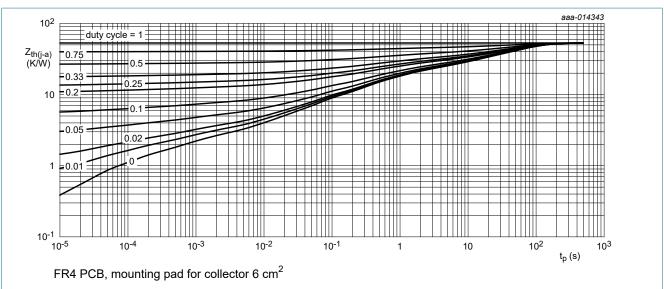


Fig. 3. Per transistor: transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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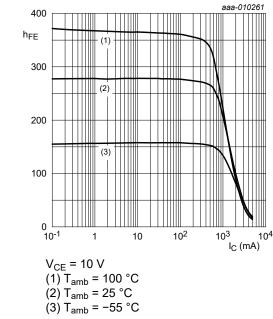
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transist	tor					
I _{CBO}	collector-base cut-off	V _{CB} = 80 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 80 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 80 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 500 mA; pulsed; $t_{p} \le$ 300 μs; $δ \le$ 0.02; T_{amb} = 25 °C	150	250	-	
		V_{CE} = 10 V; I_{C} = 1 A; pulsed; $t_{p} \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	80	250	-	
		V_{CE} = 10 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	20	100	-	
		V_{CE} = 10 V; I_{C} = 3 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	10	40	-	
V _{CEsat} collector-emitter saturation voltage		I_C = 1 A; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	90	150	mV
		I_C = 3 A; I_B = 300 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	225	330	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = 3 A; I_B = 0.3 A; pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	75	110	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 50 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.86	1	V
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	1	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 0.1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.67	0.85	V
t _d	delay time	V_{CC} = 12.5 V; I_{C} = 1 A; I_{Bon} = 50 mA;	-	20	-	ns
t _r	rise time	I _{Boff} = -50 mA; T _{amb} = 25 °C	-	300	-	ns
t _{on}	turn-on time		-	320	-	ns
t _s	storage time		-	830	-	ns
t _f	fall time		-	470	-	ns
t _{off}	turn-off time		-	1300	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	-	140	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	11	-	pF

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$$V_{CE} = 10 \text{ V}$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$



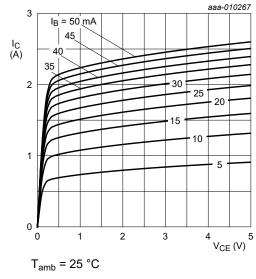
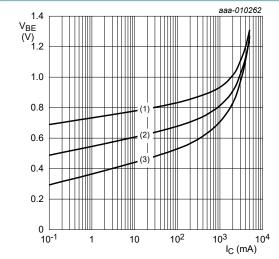


Fig. 5. Collector current as a function of collectoremitter voltage; typical values



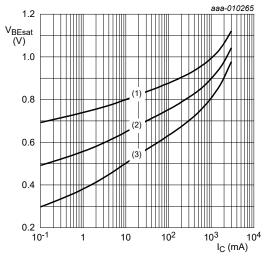


$$(1) T_{amb} = -55 °C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) T_{amb} = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B}=20$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

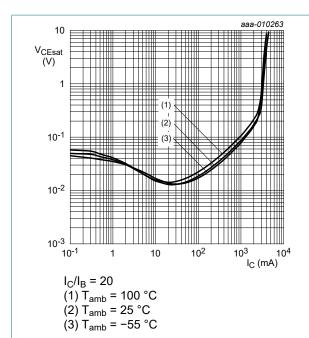


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

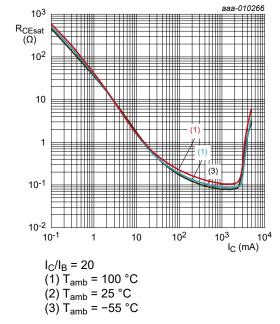


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

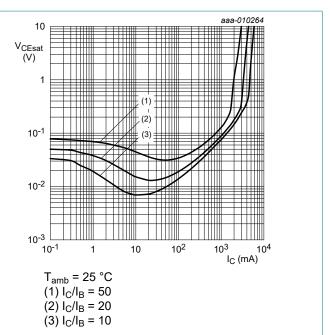


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

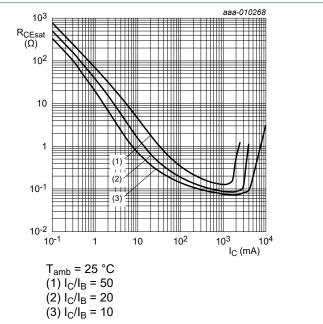
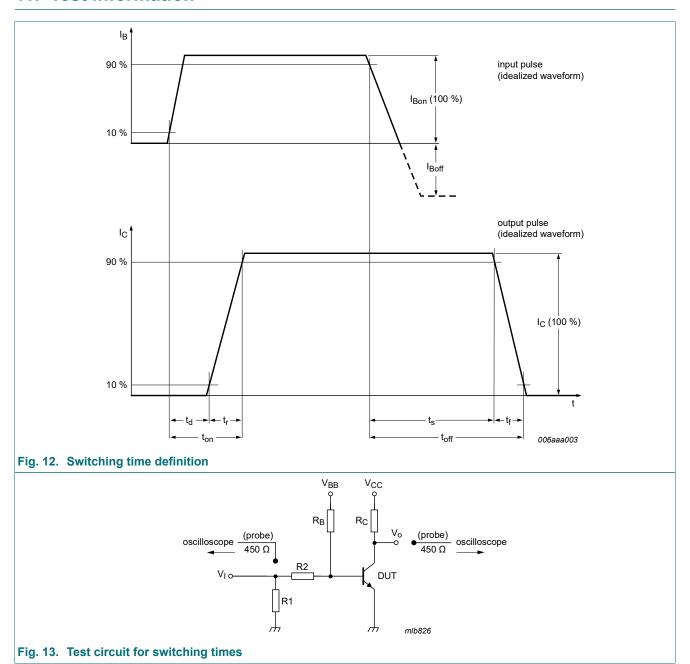


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

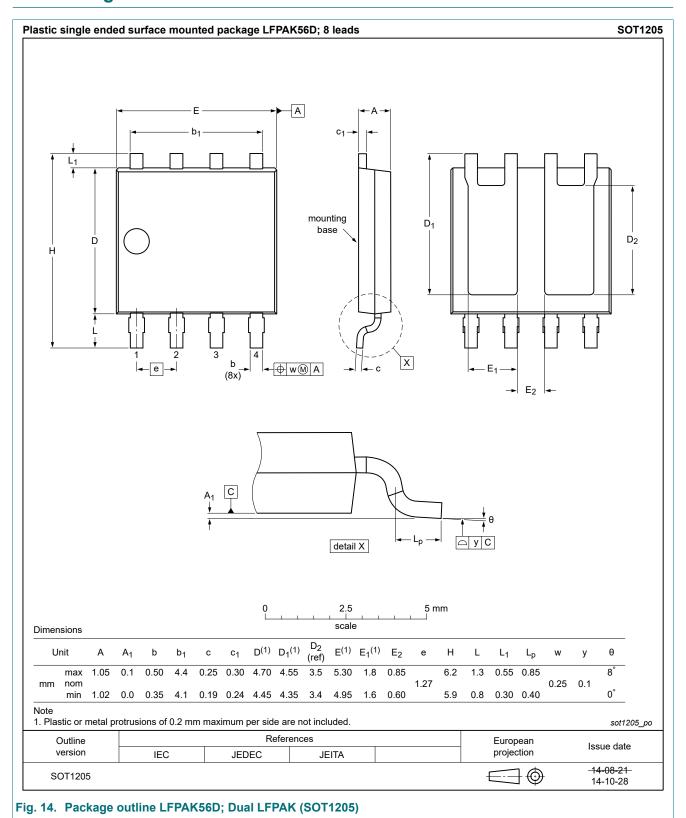
11. Test information



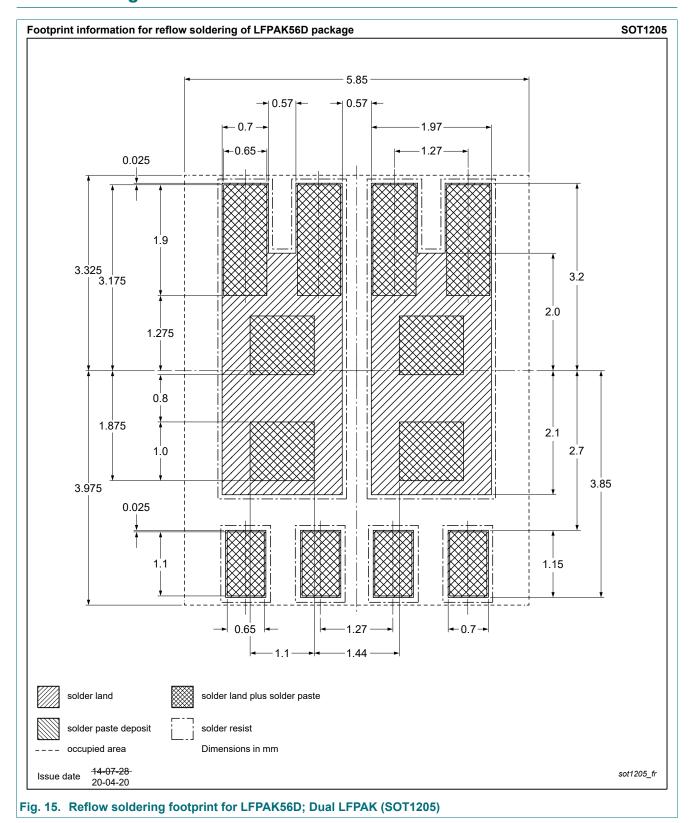
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT610030NK-Q v.1	20230210	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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